Single-crystalline In$_2$S$_3$ nanowires based flexible visible-light photodetectors with ultra-high photoresponse

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Figure S1. XRD pattern of the as-synthesized In$_2$S$_3$ NWs.

Figure S2. Schematic illustration of the single NW back gate FETs and the corresponding SEM image.
Figure S3. (a) Drain current versus drain voltage curves, and (b) Drain current versus gate voltage of the In$_2$S$_3$ NW FETs.

Figure S4. I-V curve of the flexible In$_2$S$_3$ NW photodetector in the dark.